



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

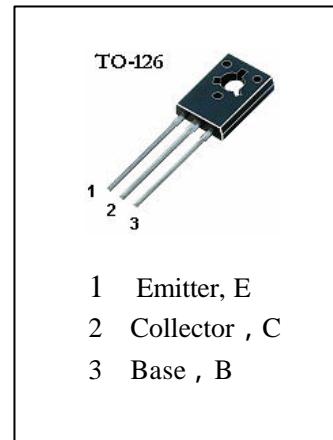
HSBD440

APPLICATIONS

Medium Power Linear switching Applications

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

| | | |
|-----------|--|---------|
| T_{stg} | Storage Temperature..... | -55~150 |
| T_j | Junction Temperature..... | 150 |
| P_c | Collector Dissipation ($T_c=25^\circ C$) | 36W |
| V_{CBO} | Collector-Base Voltage..... | -60V |
| V_{CEO} | Collector-Emitter Voltage..... | -60V |
| V_{CES} | Collector-Emitter Voltage..... | -60V |
| V_{EBO} | Emitter-Base Voltage..... | -5V |
| I_c | Collector Current(Pulse)..... | -7A |
| I_c | Collector Current(DC)..... | 4A |
| I_B | Base Current..... | -1A |



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

| Symbol | Characteristics | Min | Typ | Max | Unit | Test Conditions |
|-----------------|--------------------------------------|-----|-------|------|---------|---------------------------|
| I_{CBO} | Collector Cut-off Current | | | -100 | μA | $V_{CB}=-60V, I_E=0$ |
| I_{EBO} | Emitter Cut-off Current | | | -1 | mA | $V_{EB}=-5V, I_C=0$ |
| I_{CES} | Collector Cut-off Current | | | -100 | μA | $V_{CE}=-60V, V_{EB}=0$ |
| * $HFE(1)$ | DC Current Gain | 20 | 140 | | | $V_{CE}=-5V, I_C=-10mA$ |
| * $HFE(2)$ | DC Current Gain | 40 | 140 | | | $V_{CE}=-1V, I_C=-500mA$ |
| * $HFE(3)$ | DC Current Gain | 25 | | | | $V_{CE}=-1V, I_C=-2A$ |
| * $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | | | -0.8 | V | $I_C=-2A, I_B=-0.2A$ |
| * $V_{BE(on1)}$ | Base-Emitter On Voltage | | -0.58 | | V | $V_{CE}=-5V, I_C=-10mA$ |
| * $V_{BE(on2)}$ | Base-Emitter On Voltage | | | -1.5 | V | $V_{CE}=-1V, I_C=-2A$ |
| $V_{CEO(sus)}$ | Collector-Emitter Sustaining Voltage | -60 | | | V | $I_C=-100mA, I_B=0$ |
| f_t | Current Gain-Bandwidth Product | 3 | | | MHz | $V_{CE}=-1V, I_C=-250mA,$ |

* Pulse Test: PW=300 μs , Duty Cycle=1.5% Pulsed